

④ Drafts

④ Pending

④ Active

- ④ I1: (1) ("6709982").PN.
- ④ I2: (119) fin adj field adj effect or (FinFET)
- ④ I3: (59) 2 and fin.clm.
- ④ I4: (30) 3 and (transistor.clm. or transistor.ab.)
- ④ I5: (23) 4 and ((trench\$2 or hole\$1 or opening\$1)

④ Failed

- ④ Saved
- ④ (0) ("thinadjfilm)nearresistor").PN.
- ④ (0) ("thinadjfilm)nearresistor").PN.
- ④ (150130) thin adj film
- ④ (14857) (thin adj film) and resistor
- ④ (2054) ((thin adj film) and resistor) and ((thin adj film)
- ④ (1735) (((thin adj film) and resistor) and ((thin adj film)
- ④ (801) (((thin adj film) and resistor) and ((thin adj film)
- ④ (499) (((thin adj film) and resistor) and ((thin adj film)
- ④ (124) (((((thin adj film) and resistor) and ((thin adj fil
- ④ (34) (((((thin adj film) and resistor) and ((thin adj fil
- ④ (98) (((((thin adj film) and resistor) and ((thin adj film)
- ④ (1010) (dual adj damas55).clm.

J and ((trench\$2 or hole\$1 or opening\$1)

U	I	P	P	Document ID	Issue Date	Pages	Title	Current OR	Current XN	Patent Level	Inventor	SIC
1	1	1	1	US	20040513	12	FIN field effect	438/157	257/661	5	Gambino, Jeffrey P. et al.	438/157
				US	2004092060	12	transistor with self-al	257/E21.41	257/E21.41	5	Lin, Ming-Ren et al.	438/157
2	1	1	1	US	20040422	17	Double and triple gate	257/288	257/E21.41	5	Fried, David M. et al.	438/157
				US	2004075122	17	MOSEFT devices and meth	257/288	257/E21.41	5	Abadeer, Waqdi W. et al.	438/157
3	1	1	1	US	20040226	18	Multiple-plane FinFET	438/151	438/152;	5	Lochtefeld, Anthony J. et al.	438/157
				US	20040038464	18	CMOS	438/151	438/158	5	Clark, William F. et al.	438/157
4	1	1	1	US	20040226	48	Concurrent Fin-FET and	257/347	257/E21.70	3	Fried, David M. et al.	438/157
				US	20040036118	48	thick-body device fabri	257/347	257/E21.70	3	Clark, William F. et al.	438/157
5	1	1	1	US	20040219	64	Strained-semiconductor-	257/233	257/235;	3	Clark, William F. et al.	438/157
				US	20040031979	64	on-insulator device str	257/233	257/297;	3	Clark, William F. et al.	438/157
6	1	1	1	US	20031030	24	Strained fin fets	257/192	257/E21.41	11	Fried, David M. et al.	438/157
				US	20030201458	24	structure and method	257/192	257/E21.41	11	Clark, William F. et al.	438/157
7	1	1	1	US	20031023	19	FIN MEMORY CELL AND	257/200	257/200	11	Fried, David M. et al.	438/157
				US	20030197194	19	257/200	257/200	257/200	11	Clark, William F. et al.	438/157
8	1	1	1	US	20030925	38	Strained fin FETs	257/347	257/E21.41	11	Fried, David M. et al.	438/157
				US	20030178681	38	structure and method	257/347	257/E21.41	11	Clark, William F. et al.	438/157
9	1	1	1	US	20030925	38	STRAINED FIN FETS	257/347	257/E21.41	11	Fried, David M. et al.	438/157
				US	20030178677	38	STRUCTURE AND METHOD	257/347	257/E21.41	11	Clark, William F. et al.	438/157
10	1	1	1	US	20030925	14	Finfet CMOS with NVRAM	257/318	257/E21.20	9	Fried, David M. et al.	438/157
				US	20030178670	14	capability	257/318	257/E21.20	9	Clark, William F. et al.	438/157
11	1	1	1	US	20030605	22	Finfet SRAM cell using	257/401	257/350;	9	Fried, David M. et al.	438/157
				US	20030102518	22	low mobility plane for	257/401	257/368;	9	Fried, David M. et al.	438/157
12	1	1	1	US	20030605	18	Multiple-plane finFET	257/255	257/255	18	Fried, David M. et al.	438/157